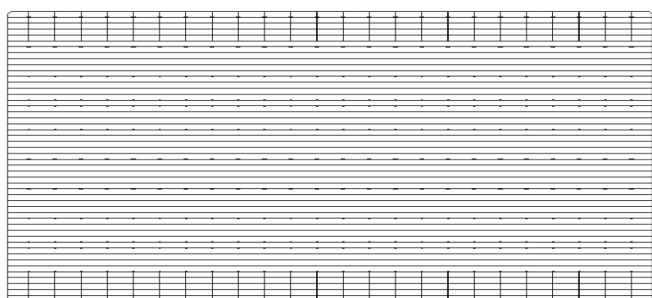


High Efficiency HJT Cell

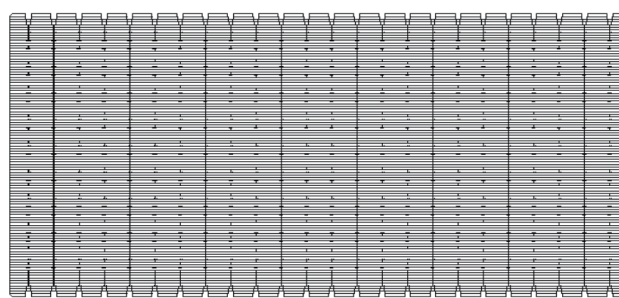
G12 | 210 Half-cut Bifacial

RHA-H02-02-00

| Cell Drawing



Front



Back

| Advantages



Efficiency

Average efficiency over 26.2%



Mass Production

Mass production capability of 110um-thick silicon



Power Generation

Power generation gain up to 5%+



Temperature

Production temperature less than 250°C



Bifacial Coefficient

High bifacial coefficient of > 90%



Yield

Average yield up to 99%



Technique

4-6 step technique



No Attenuation

No PID. LID effect



Wastewater

Zero NH3-N Wastewater



Temperature Coefficient

Lower temperature coefficient

Main Parameters

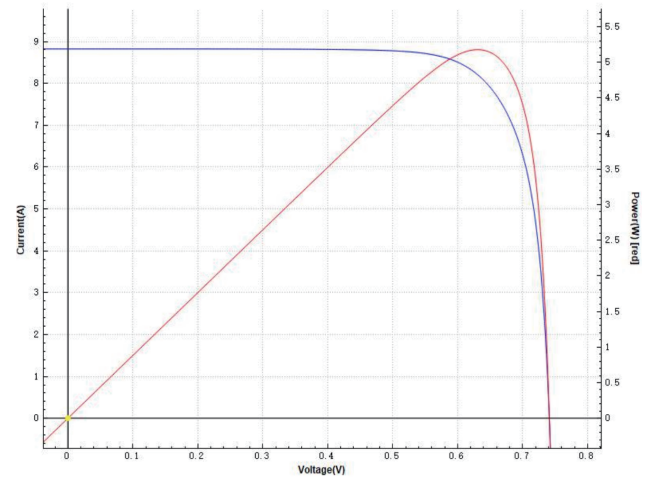
Eff (%)	Pmpp(W)	Uoc(V)	Isc (A)	FF (%)	Umpp(V)	Impp(A)
26.30	5.80	0.753	8.835	87.18	0.685	8.467
26.20	5.78	0.753	8.824	86.94	0.684	8.445
26.10	5.75	0.752	8.817	86.79	0.683	8.425
26.00	5.73	0.752	8.810	86.53	0.682	8.405
25.90	5.71	0.751	8.796	86.45	0.681	8.385
25.80	5.69	0.750	8.780	86.38	0.680	8.365
25.70	5.67	0.750	8.769	86.16	0.679	8.345
25.60	5.64	0.750	8.759	85.92	0.679	8.313
25.50	5.62	0.749	8.745	85.84	0.678	8.292
25.40	5.60	0.749	8.734	85.61	0.678	8.260
25.30	5.58	0.748	8.725	85.47	0.677	8.240
25.20	5.56	0.748	8.715	85.23	0.676	8.219
25.10	5.53	0.748	8.709	84.95	0.675	8.199
25.00	5.51	0.747	8.699	84.82	0.674	8.178

*Standard Test Condition: Irradiance 1000W/m², Temperature 25°C, Air Mass 1.5;
The above parameters are subject to conditions,

Temp. Coefficient

Voc (%/°C)	~-0.27%/°C
Isc (%/°C)	~0.055%/°C
Pm (%/°C)	~-0.258%/°C

Characteristic Curve



Specification

Size	210 mm*105 mm±0.25 mm
Material	n-type mono crystalline silicon
Thickness	110±20 μm
Front (-)	0 bus bars, Blue transparent conductive film(TCO)
Back (+)	0 bus bars, Blue transparent conductive film(TCO)

Packaging Information

Quantity	24case/box, 140pcs/case, 3360pcs/box
Size	60cm*30cm*30.5cm